



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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## Product Summary

$BV_{DSS}$	$R_{DS(ON)}$ Max	$I_D$ Max $T_A = +25^\circ C$
50V	$3.5\Omega @ V_{GS} = 10V$	200mA

## Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed

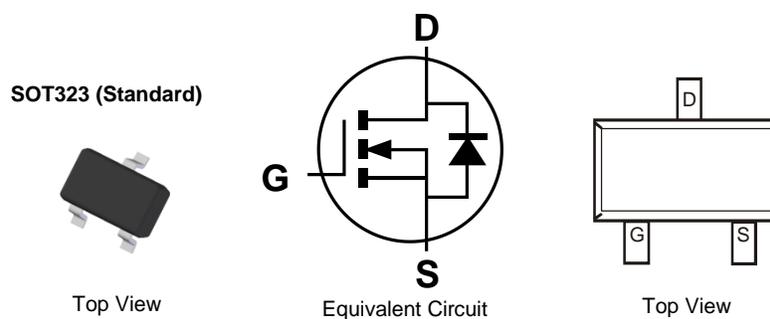
## Description and Applications

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

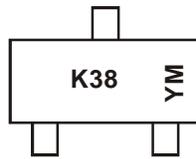
- Load Switch

## Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)

## Marking Information



K38 = Product Type Marking Code  
YM = Date Code Marking  
Y or  $\bar{Y}$  = Year (ex: I = 2021)  
M or  $\bar{M}$  = Month (ex: 9 = September)

### Date Code Key

Year	2003	...	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	P	...	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

## Maximum Ratings (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	50	V
Drain-Gate Voltage (Note 5)	$V_{DGR}$	50	V
Gate-Source Voltage	$V_{GS}$	+20	V
Drain Current (Note 6)	$I_D$	200	mA

## Thermal Characteristics (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	$P_D$	200	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

## Electrical Characteristics (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	50	75	—	V	$V_{GS} = 0V, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	0.5	$\mu\text{A}$	$V_{DS} = 50V, V_{GS} = 0V$
Gate-Body Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	0.5	1.2	1.5	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	1.4	3.5	$\Omega$	$V_{GS} = 10V, I_D = 0.22A$
Forward Transconductance	$g_{FS}$	100	—	—	mS	$V_{DS} = 25V, I_D = 0.2A, f = 1.0\text{kHz}$
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	$C_{iss}$	—	—	50	pF	$V_{DS} = 10V, V_{GS} = 0V, f = 1.0\text{MHz}$
Output Capacitance	$C_{oss}$	—	—	25	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	—	8.0	pF	
Turn-On Delay Time	$t_{D(ON)}$	—	—	20	ns	$V_{DD} = 30V, I_D = 0.2A, R_{GEN} = 50\Omega$
Turn-Off Delay Time	$t_{D(OFF)}$	—	—	20	ns	

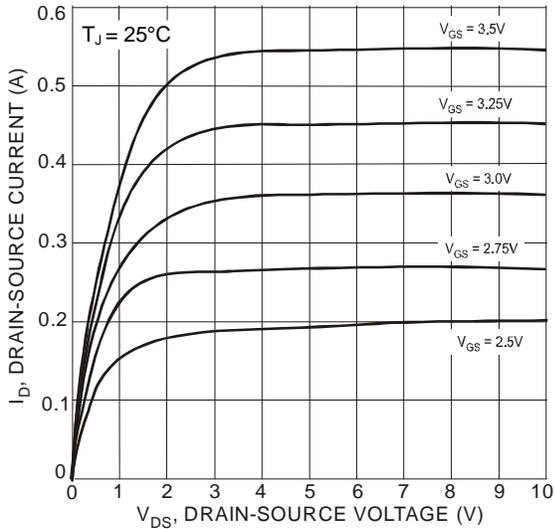


Fig. 1 Drain-Source Current vs. Drain-Source Voltage

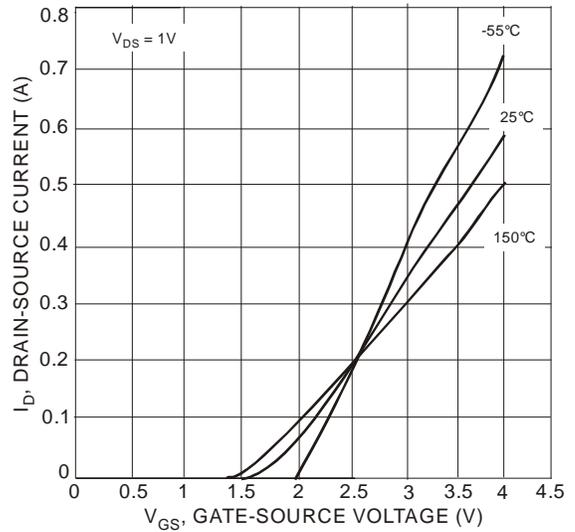


Fig. 2 Transfer Characteristics

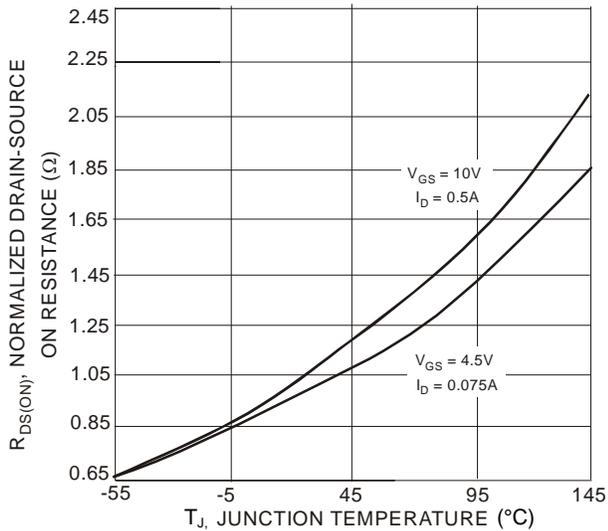


Fig. 3 Drain-Source On Resistance vs. Junction Temperature

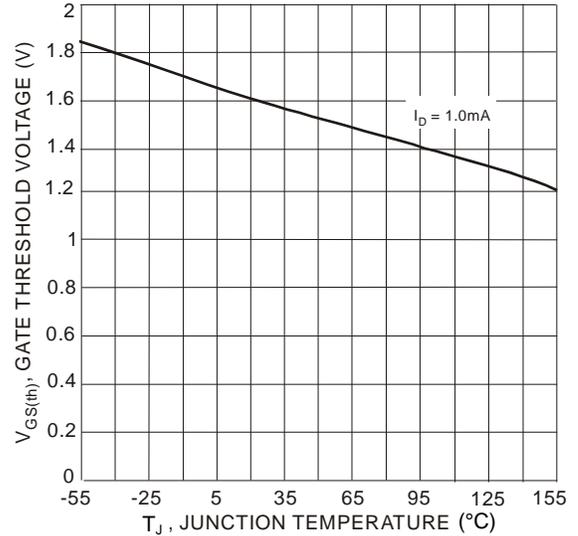


Fig. 4 Gate Threshold Voltage vs. Junction Temperature

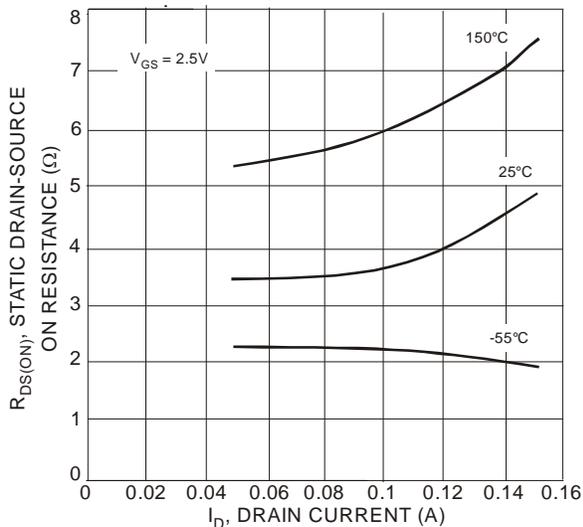


Fig. 5 Drain-Source On Resistance vs. Drain Current

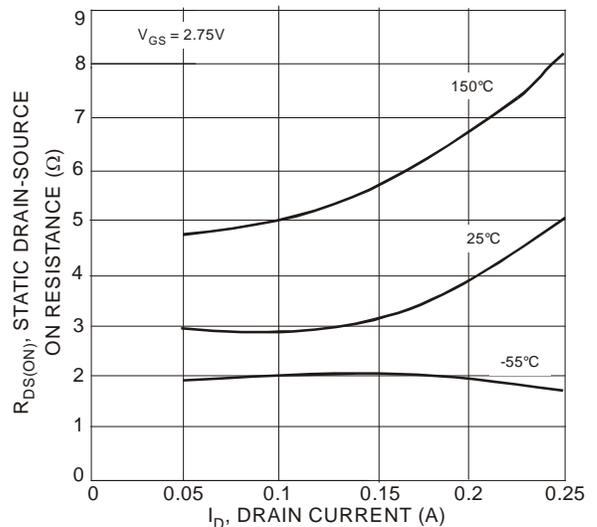


Fig. 6 Drain-Source On Resistance vs. Drain Current

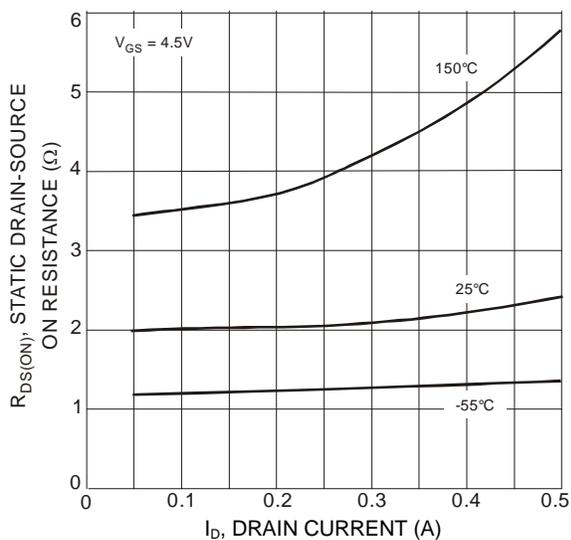


Fig. 7 Drain-Source On Resistance vs. Drain Current

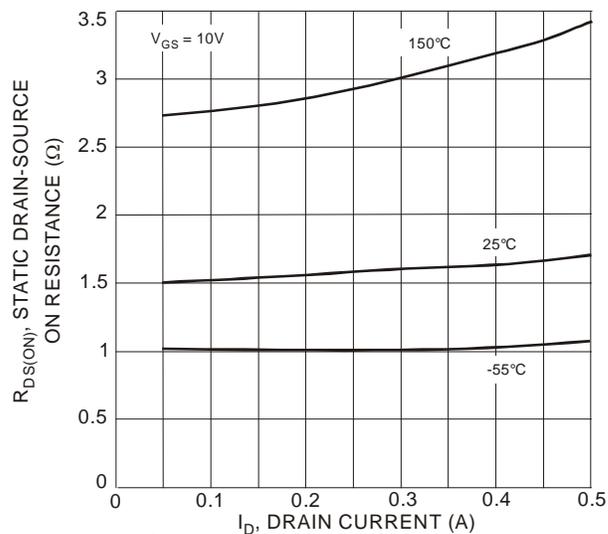


Fig. 8 Drain-Source On Resistance vs. Drain Current

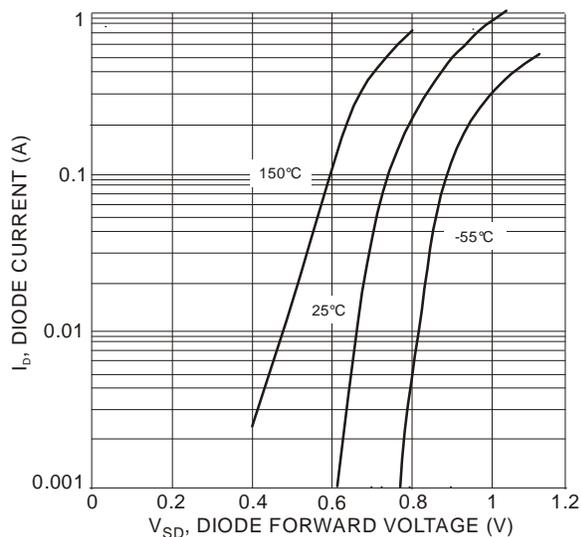


Fig. 9 Body Diode Current vs. Body Diode Voltage

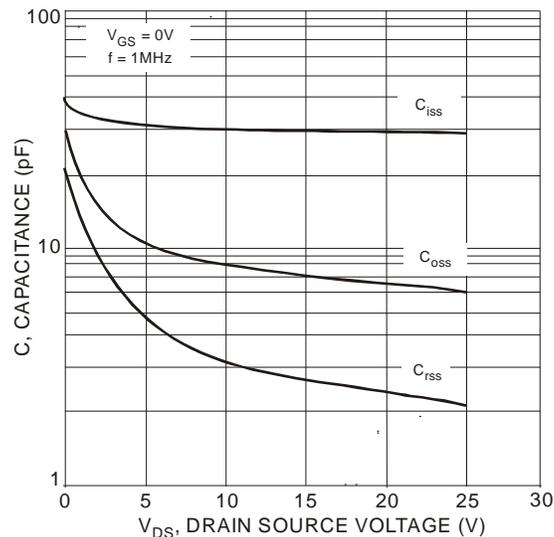
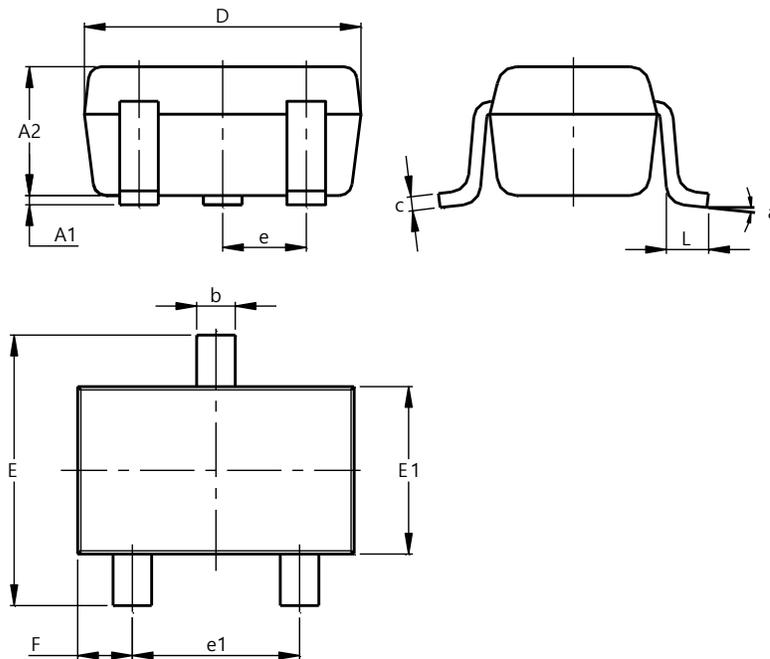


Fig. 10 Capacitance vs. Drain Source Voltage

## Package Outline Dimensions

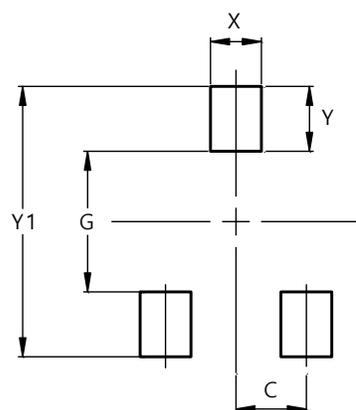
SOT323 (Standard)



SOT323 (Standard)			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.80	1.00	0.90
b	0.20	0.40	0.30
c	0.08	0.18	0.13
D	1.80	2.20	2.00
E	2.00	2.45	2.225
E1	1.15	1.35	1.25
e	--	--	0.65
e1	1.20	1.40	1.30
F	0.25	0.475	0.3625
L	0.25	0.46	0.355
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

SOT323 (Standard)



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500